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FDP12N60NZ / FDPF12N60NZ N-Channel UniFETTM II MOSFET 600 V, 12 A, 650 m Ω

Features

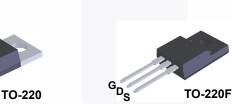
- $R_{DS(on)}$ = 530 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 6 A
- Low Gate Charge (Typ. 26 nC)
- Low C_{rss} (Typ. 12 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- ESD Improved Capability
- RoHS Compliant

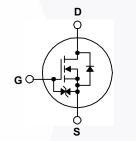
Applications

- LCD/ LED/ PDP TV
- Lighting
- Uninterruptible Power Supply

Description

UniFETTM II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp balasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

| | FDP12N60NZ | FDPF12N60NZ | Unit | | | |
|--|--|--|---|--|--|--|
| Drain to Source Voltage | | | 6 | V | | |
| Gate to Source Voltage | | | ± | V | | |
| Drain Current | - Continuous (T _C = 25 ^o C) | | 12 | 12* | • | |
| Drain Current | - Continuous (T _C = 100 ^o C) | | 7.2 | 7.2* | A | |
| Drain Current | - Pulsed | 48 | 48* | А | | |
| Single Pulsed Avalanche Energy (Note 2) | | | 5 | mJ | | |
| Avalanche Current | | (Note 1) | 12 | | А | |
| Repetitive Avalanche Energy | | (Note 1) | 24 | | mJ | |
| MOSFET dv/dt Ruggedness | | | 20 | | V/ns | |
| Peak Diode Recovery dv/dt | | (Note 3) | 10 | | V/ns | |
| Deuver Dissignation | (T _C = 25°C) | | 240 | 39 | W | |
| Fower Dissipation | - Derate Above 25°C | | 2.0 | 0.3 | W/ºC | |
| Operating and Storage Temperature Range | | | -55 to | °C | | |
| Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | | | 3 | °C | | |
| | Gate to Source Voltage Drain Current Drain Current Single Pulsed Avalanche E Avalanche Current Repetitive Avalanche Ener MOSFET dv/dt Ruggednes Peak Diode Recovery dv/d Power Dissipation Operating and Storage Ter | Gate to Source Voltage Drain Current - Continuous ($T_C = 25^{\circ}C$) Drain Current - Pulsed Single Pulsed Avalanche Energy Avalanche Current Repetitive Avalanche Energy MOSFET dv/dt Ruggedness Peak Diode Recovery dv/dt Power Dissipation $(T_C = 25^{\circ}C)$ - Derate Above 25^{\circ}C Operating and Storage Temperature Range | $\begin{array}{c c c c c c c } \hline Drain to Source Voltage \\ \hline Gate to Source Voltage \\ \hline Gate to Source Voltage \\ \hline \\ \hline \\ Gate to Source Voltage \\ \hline \\ \hline \\ \hline \\ \\ \hline \\ Drain Current \\ \hline \\ \hline \\ \\ Drain Current \\ \hline \\ \hline \\ \\ \hline \\ \\ Drain Current \\ \hline \\ \\ \hline \\ \\ \hline \\ \\ \hline \\ \\ \\ \hline \\ \\ \\ \\ $ | $\begin{array}{c c c c c c c } \hline Drain to Source Voltage & & & & & & & & & & & & & & & & & & &$ | $\begin{array}{c c c c c c c } \hline Drain to Source Voltage & 600 \\ \hline Gate to Source Voltage & \pm 30 \\ \hline Gate to Source Voltage & & & & & & \\ \hline Gate to Source Voltage & & & & & & & \\ \hline Gate to Source Voltage & & & & & & & \\ \hline Drain Current & & & & & & \\ \hline Drain Current & & & & & & & & \\ \hline Drain Current & & & & & & & & \\ \hline Drain Current & & & & & & & & \\ \hline Drain Current & & & & & & & & \\ \hline Drain Current & & & & & & & & \\ \hline Pulsed & (Note 1) & 48 & & & & & & \\ \hline Single Pulsed Avalanche Energy & (Note 2) & & & & & \\ \hline Avalanche Current & & & & & & & & \\ \hline Avalanche Current & & & & & & & & \\ \hline Avalanche Current & & & & & & & & \\ \hline MOSFET dv/dt Ruggedness & & & & & & & & \\ \hline Peak Diode Recovery dv/dt & & & & & & & & & \\ \hline Power Dissipation & & & & & & & & \\ \hline \hline Power Dissipation & & & & & & & & \\ \hline \hline Cr = 25^{\circ}C) & & & & & & & & & \\ \hline Portent and Storage Temperature Range & & & & & & & \\ \hline \end{array}$ | |

*Drain current limited by maximum junction temperature

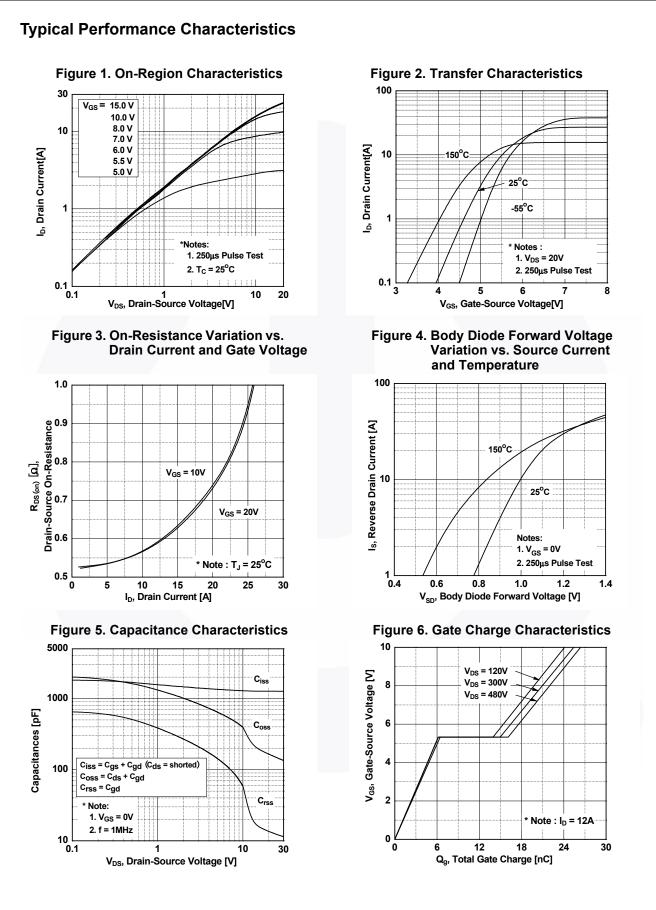
Thermal Characteristics

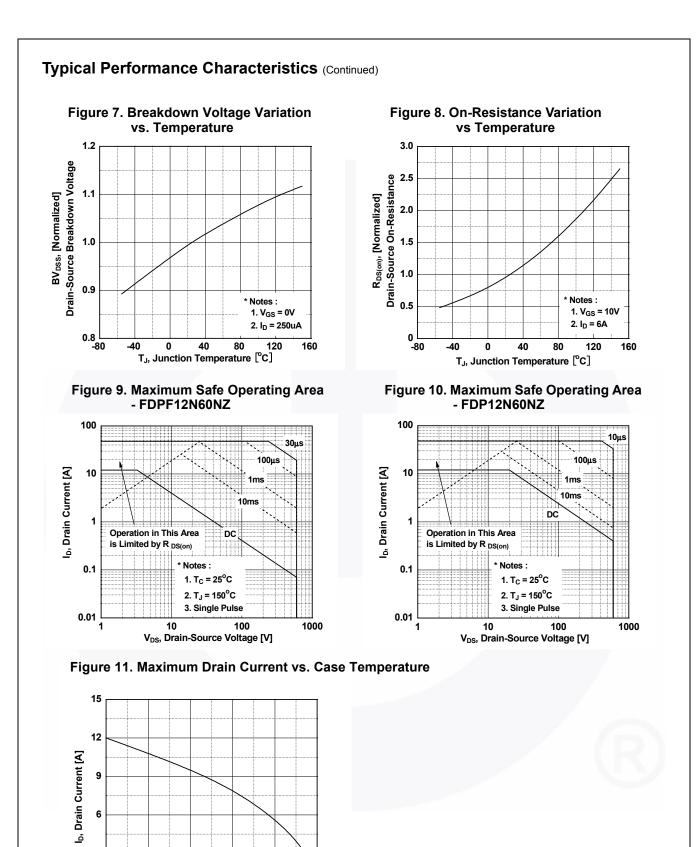
| Symbol | Parameter | FDP12N60NZ | FDPF12N60NZ | Unit | |
|-----------------------|---|------------|-------------|-------|--|
| $R_{	extsf{	heta}JC}$ | Thermal Resistance, Junction to Case, Max. | 0.52 | 3.2 | °C/W | |
| $R_{	extsf{	heta}JA}$ | Thermal Resistance, Junction to Ambient, Max. | 62.5 | 62.5 | -0/00 | |

November 2013

| Part Number Top Ma | | Top Mark | Package | Packing Method | Reel Size |) T | ape Width | Qu | antity | |
|----------------------------|---|-----------------------------------|-----------------|--|----------------------------------|------|-----------|----------|--------|--|
| FDP12N | FDP12N60NZ FDP12N60NZ | | TO-220 | Tube | N/A | | N/A | 50 units | | |
| FDPF12 | | | TO-220F | TO-220F Tube N/A | | N/A | | 50 units | | |
| Electrica | l Chara | acteristics T _C = 25°C | unless othe | erwise noted. | | | | | | |
| Symbol | | Parameter | | Test Condition | s | Min. | Тур. | Max. | Unit | |
| - Off Charac | teristics | | | | L. L. L. | | | | 1 | |
| BV _{DSS} | Drain to | Source Breakdown Voltage | In = | 250 μA, V _{GS} = 0 V, T | ₁ = 25 ^o C | 600 | - | - | V | |
| ΔBV _{DSS} /ΔTJ | | wn Voltage Temperature | | $I_D = 250 \ \mu$ A, Referenced to 25° C | | - | 0.6 | - | V/°C | |
| | 7 0 1 | | V _{DS} | = 600 V, V _{GS} = 0 V | | - | - | 1 | | |
| DSS | Zero Gat | ero Gate Voltage Drain Current | | $V_{DS} = 480 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$ | | - | - | 10 | μA | |
| I _{GSS} | Gate to E | Body Leakage Current | V _{GS} | s = ±30 V, V _{DS} = 0 V | | - | - | ±10 | μΑ | |
| On Charac | teristics | | | | | | | | | |
| V _{GS(th)} | | reshold Voltage | Ves | _S = V _{DS} , I _D = 250 μA | | 3 | - | 5 | V | |
| R _{DS(on)} | | ain to Source On Resistance | | $s = 10 \text{ V}, I_D = 6 \text{ A}$ | | - | 0.53 | 0.65 | Ω | |
| 9FS | Forward | Transconductance | | _s = 20 V, I _D = 6 A | | - | 13.5 | - | S | |
| Dynamic C | Characte | ristics | | | | | | | | |
| C _{iss} | 1 | pacitance | | | | - | 1260 | 1676 | pF | |
| C _{oss} | | apacitance | | $_{\rm S} = 25 \text{ V}, \text{ V}_{\rm GS} = 0 \text{ V},$ | - | 150 | 200 | pF | | |
| C _{rss} | | Transfer Capacitance | t = 1 | f = 1 MHz | | - | 12 | 18 | pF | |
| Q _{g(tot)} | | e Charge at 10V | V | V _{DS} = 480 V, I _D = 12 A, V _{GS} = 10 V (Note 4) | | - | 26 | 34 | nC | |
| Q _{gs} | | Source Gate Charge | | | | - | 6 | - | nC | |
| Q _{gd} | Gate to D | Drain "Miller" Charge | 0 | | | - | 10 | - | nC | |
| Switching | Charact | eristics | | | | | | | | |
| t _{d(on)} | - | Delay Time | | V _{DD} = 300 V, I _D = 12 A, | | - | 25 | 60 | ns | |
| t _r | | Rise Time | VDD | | | - | 50 | 110 | ns | |
| t _{d(off)} | | Delay Time | V _{GS} | $_{\rm S}$ = 10 V, R _G = 25 Ω | - | | 80 | 170 | ns | |
| t _f | | Fall Time | | | (Note 4) | | 60 | 130 | ns | |
| Drain-Sou | rce Diod | e Characteristics | | | | | 11 | | | |
| I _S | 1 | Continuous Drain to Source | e Diode For | ward Current | | | _ | 12 | А | |
| I _{SM} | Maximum Pulsed Drain to Source Diode Fo | | | | | - | _ | 48 | A | |
| V _{SD} | Drain to Source Diode Forward Voltage | | | $V_{GS} = 0 V, I_{SD} = 12 A$ | | - | - | 1.4 | V | |
| t _{rr} | | Recovery Time | | $V_{GS} = 0 V, I_{SD} = 12 A,$ | | - | 350 | · • · | ns | |
| Q _{rr} | Reverse Recovery Charge | | | $dI_{\rm F}/dt = 100 \text{ A}/\mu \text{s}$ | | - | 2.2 | - | μC | |

2





T_c, Case Temperature [°C]

100

125

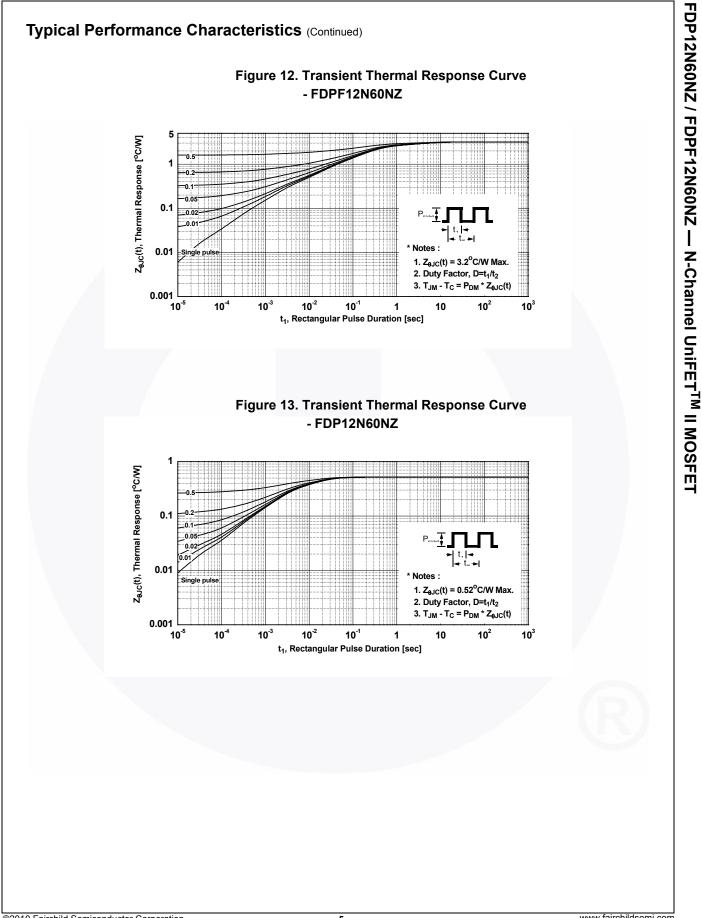
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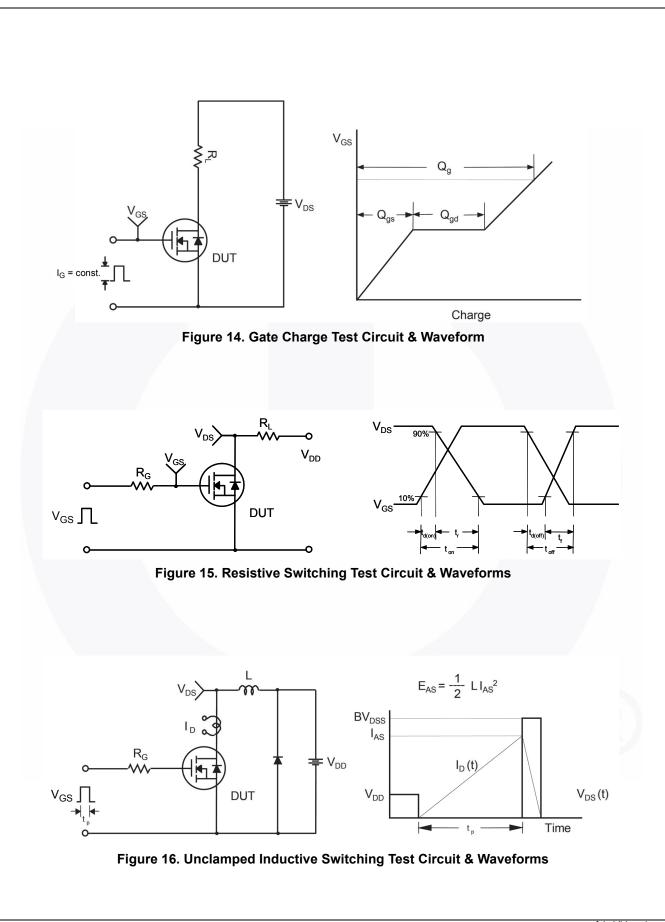
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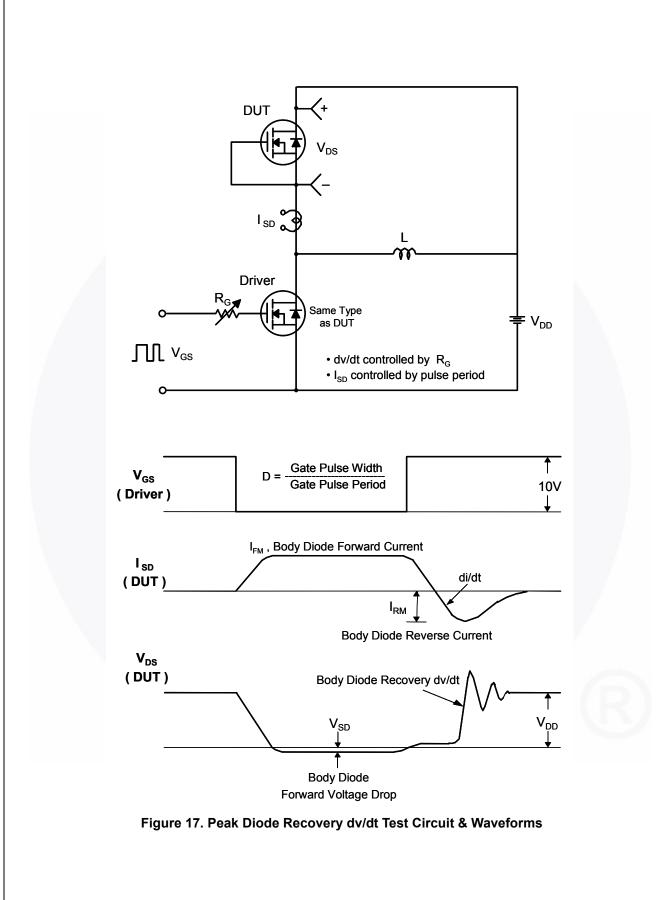
3

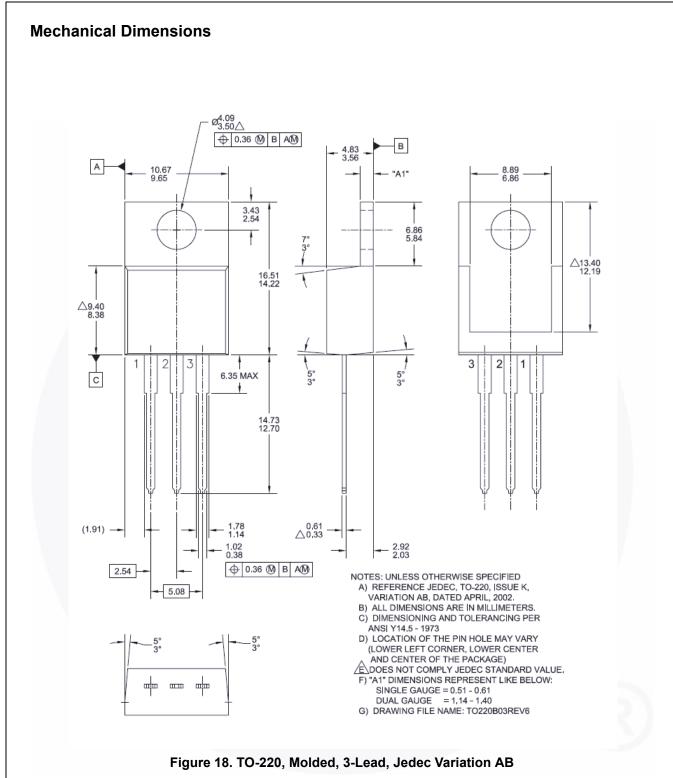
0 ∟ 25

50







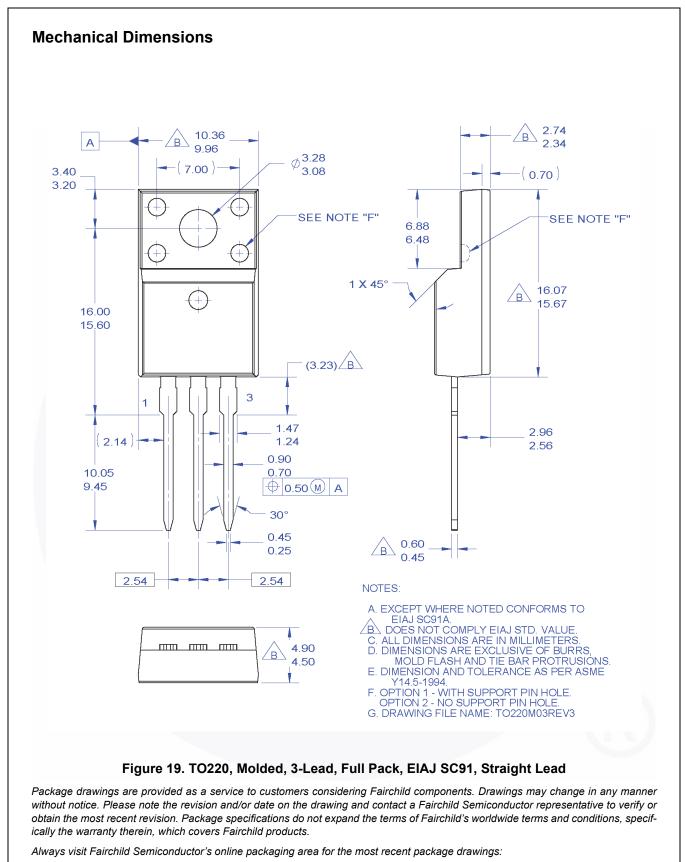


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FDP12N60NZ / FDPF12N60NZ — N-Channel UniFETTM II MOSFET



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